

# DMN61D8LQ-7 Datasheet



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DiGi Electronics Part Number	DMN61D8LQ-7-DG
Manufacturer	<a href="#">Diodes Incorporated</a>
Manufacturer Product Number	DMN61D8LQ-7
Description	MOSFET N-CH 60V 470MA SOT23
Detailed Description	N-Channel 60 V 470mA (Ta) 390mW (Ta) Surface Mount SOT-23-3



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## Purchase and inquiry

Manufacturer Product Number:

DMN61D8LQ-7

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

3V, 5V

Vgs(th) (Max) @ Id:

2V @ 1mA

Vgs (Max):

±12V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-23-3

Base Product Number:

DMN61

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

470mA (Ta)

Rds On (Max) @ Id, Vgs:

1.8Ohm @ 150mA, 5V

Gate Charge (Qg) (Max) @ Vgs:

0.74 nC @ 5 V

Input Capacitance (Ciss) (Max) @ Vds:

12.9 pF @ 12 V

Power Dissipation (Max):

390mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-236-3, SC-59, SOT-23-3

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN61D8LQ

## INTEGRATED RELAY AND INDUCTIVE LOAD DRIVER

### Product Summary

BV <sub>bss</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	1.8Ω @ V <sub>GS</sub> = 5V	470mA
	2.4Ω @ V <sub>GS</sub> = 3V	

### Description and Applications

The DMN61D8LQ provides a single component solution for switching inductive loads such as relays, solenoids, and small DC motors in automotive applications, without the need of a freewheeling diode. DMN61D8LQ accepts logic level inputs, thus allowing it to be driven by logic gates, inverters, and microcontrollers.

### Features and Benefits

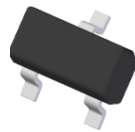
- Provides A More Reliable And Robust Interface Between Sensitive Logic And DC Relay Coils
- Replaces 3 to 4 Discrete Components Enabling PCB Footprint To Be Reduced
- Internal Active Clamp Removes The Need For External Zener Diode
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

### Mechanical Data

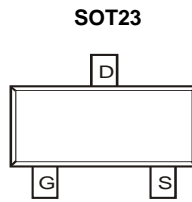
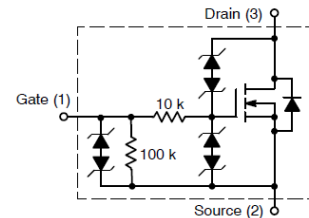
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



ESD protected



Top View

Top View  
Internal Schematic

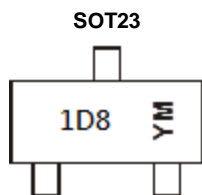
Equivalent Circuit

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMN61D8LQ-7	SOT23	3,000/Tape & Reel
DMN61D8LQ-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

### Marking Information



1D8 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

#### Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022					
Code	D	E	F	G	H	I	J					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMN61D8LQ

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	$\pm 12$	V
Continuous Drain Current (Note 7)	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	470	mA
		$T_A = +70^\circ\text{C}$		370	
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	0.5	A
Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80 $\Omega$ or Higher) ( $T_J$ Initial = $+85^\circ\text{C}$ )			$E_Z$	200	mJ
Peak Power Dissipation, Drain-to-Source (Non repetitive current square pulse 1.0ms duration) ( $T_J$ Initial = $+85^\circ\text{C}$ )			$P_{PK}$	20	W
Load Dump Pulse, Drain-to-Source, $R_{SOURCE} = 0.5\Omega$ , $t = 300\text{ms}$ (For Relay's Coils/Inductive Loads of 80 $\Omega$ or Higher) ( $T_J$ Initial = $+85^\circ\text{C}$ )			$E_{LD1}$	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: $R_{SOURCE} = 10\Omega$ , $t = 2.0\text{ms}$ ) (For Relay's Coils/Inductive Loads of 80 $\Omega$ or Higher) ( $T_J$ Initial = $+85^\circ\text{C}$ )			$E_{LD2}$	100	V
Inductive Switching Transient 2, Drain-to-Source (Waveform: $R_{SOURCE} = 4.0\Omega$ , $t = 50\mu\text{s}$ ) (For Relay's Coils/Inductive Loads of 80 $\Omega$ or Higher) ( $T_J$ Initial = $+85^\circ\text{C}$ )			$E_{LD3}$	300	V
Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80 $\Omega$ or more)			Rev-Bat	-14	V
Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)			Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V

**Thermal Characteristics**

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 6)			$P_D$	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	321	$^\circ\text{C/W}$
Total Power Dissipation (Note 7)			$P_D$	610	mW
Thermal Resistance, Junction to Ambient (Note 7)	Steady State		$R_{\theta JA}$	208	$^\circ\text{C/W}$
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.  
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

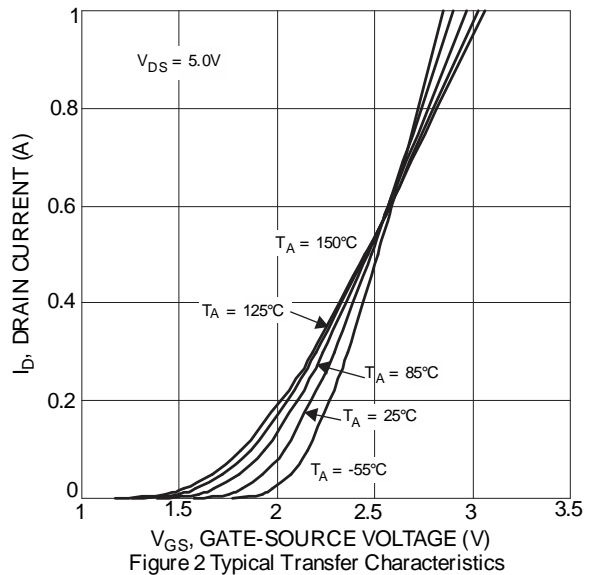
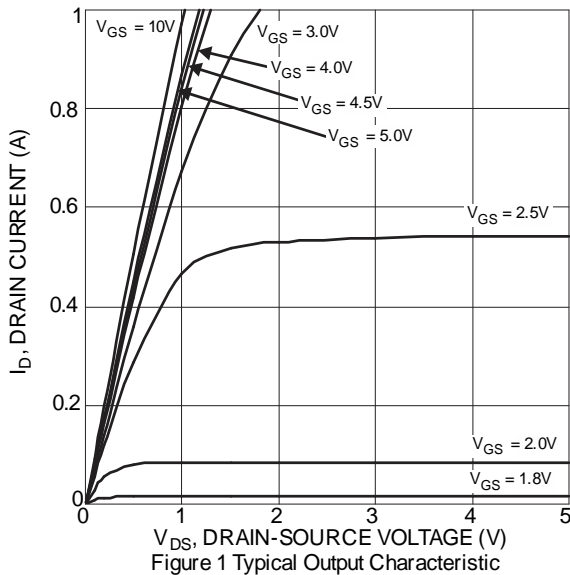


**DMN61D8LQ**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	50 0.5	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 12V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±90 ±60	μA	V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±3V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.1	1.8	Ω	V <sub>GS</sub> = 5V, I <sub>D</sub> = 0.15A
			1.4	2.4		V <sub>GS</sub> = 3V, I <sub>D</sub> = 0.15A
Forward Transfer Admittance	Y <sub>fs</sub>	80	—	—	ms	V <sub>DS</sub> = 12V, I <sub>D</sub> = 0.15A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.15A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	12.9	—	pF	V <sub>DS</sub> = 12V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	17	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	0.84	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	0.74	—	nC	V <sub>GS</sub> = 5V, V <sub>DS</sub> = 12V, I <sub>D</sub> = 150mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.19	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.16	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	131	—	ns	V <sub>DD</sub> = 12V, V <sub>GS</sub> = 5V.
Turn-On Rise Time	t <sub>r</sub>	—	301	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	582	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	440	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.





**DMN61D8LQ**

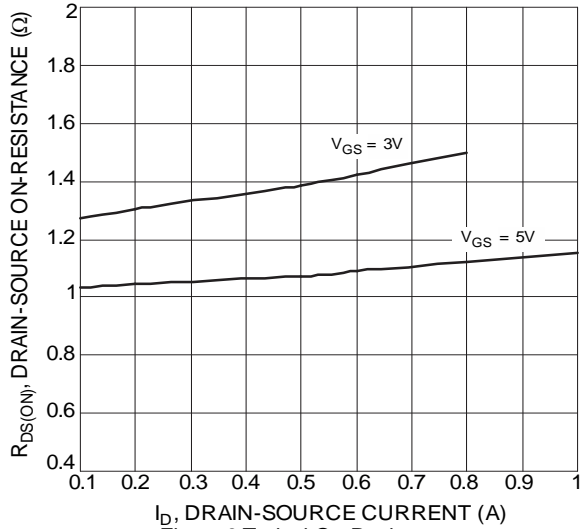


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

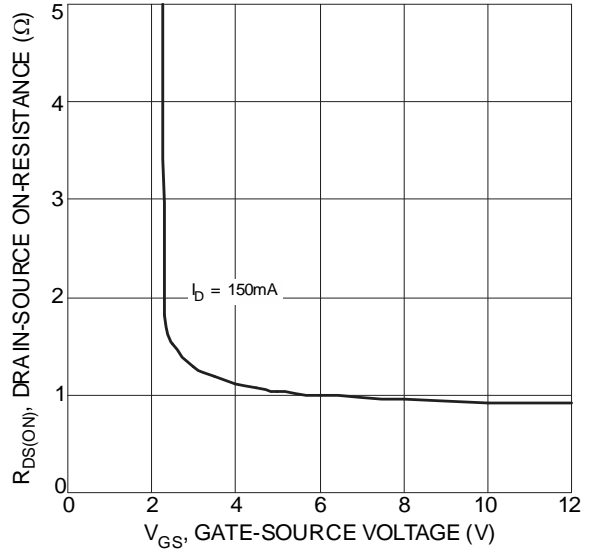


Figure 4 Typical Transfer Characteristic

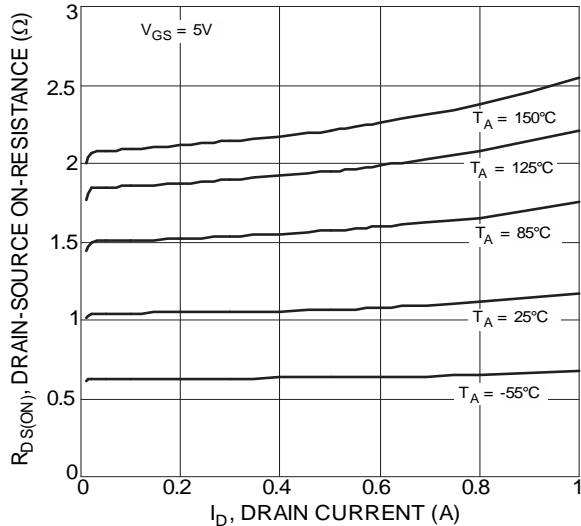


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

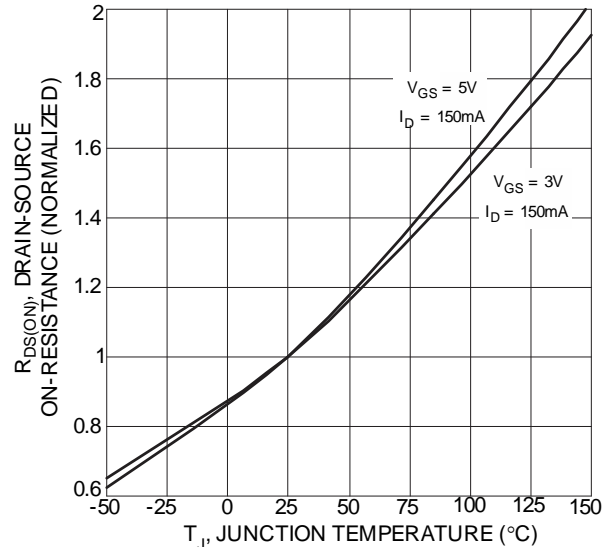


Figure 6 On-Resistance Variation with Temperature

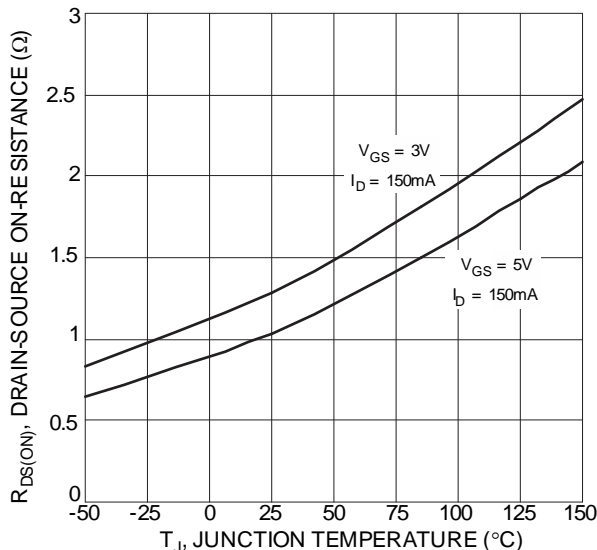


Figure 7 On-Resistance Variation with Temperature

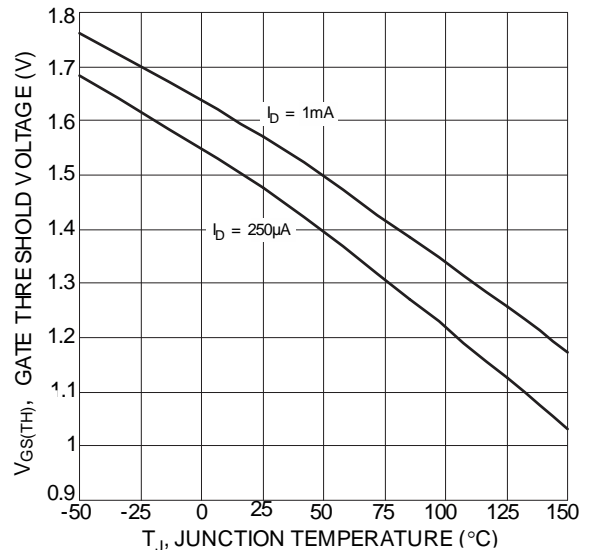


Figure 8 Gate Threshold Variation vs. Junction Temperature



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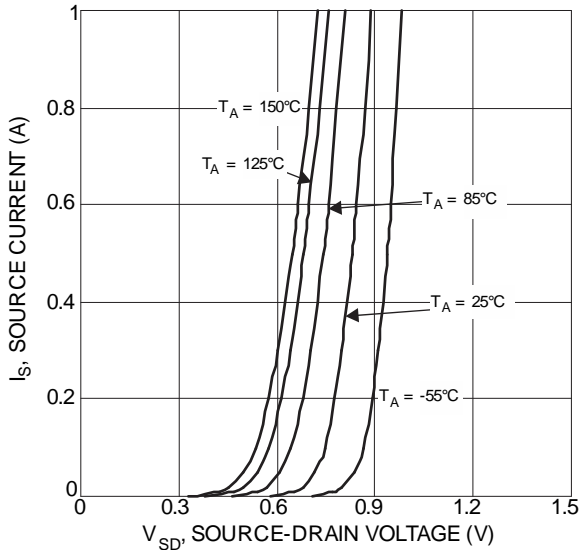


Figure 9 Diode Forward Voltage vs. Current

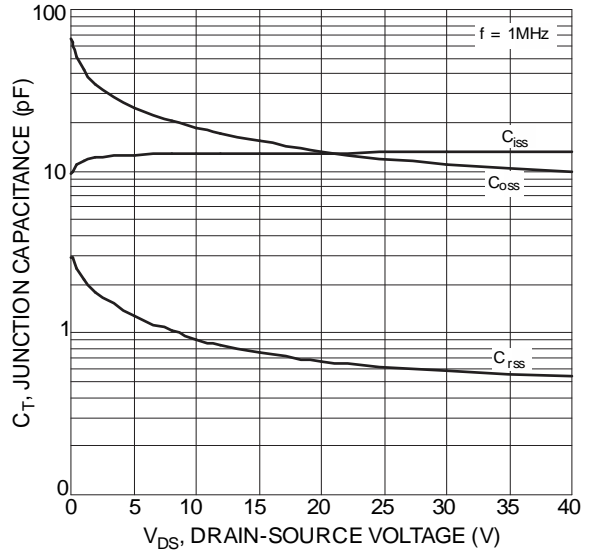


Figure 10 Typical Junction Capacitance

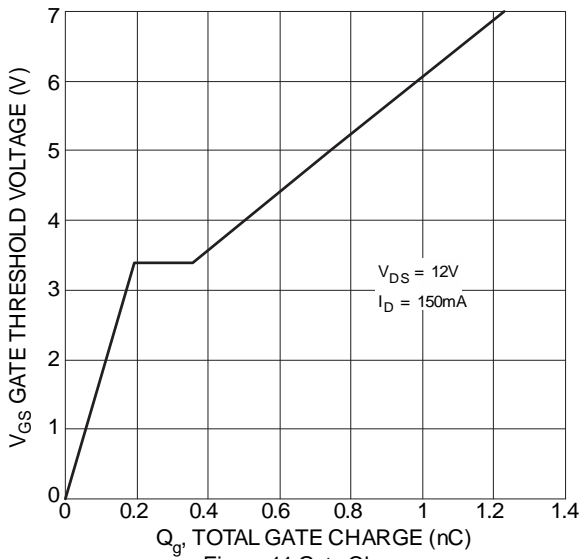


Figure 11 Gate Charge

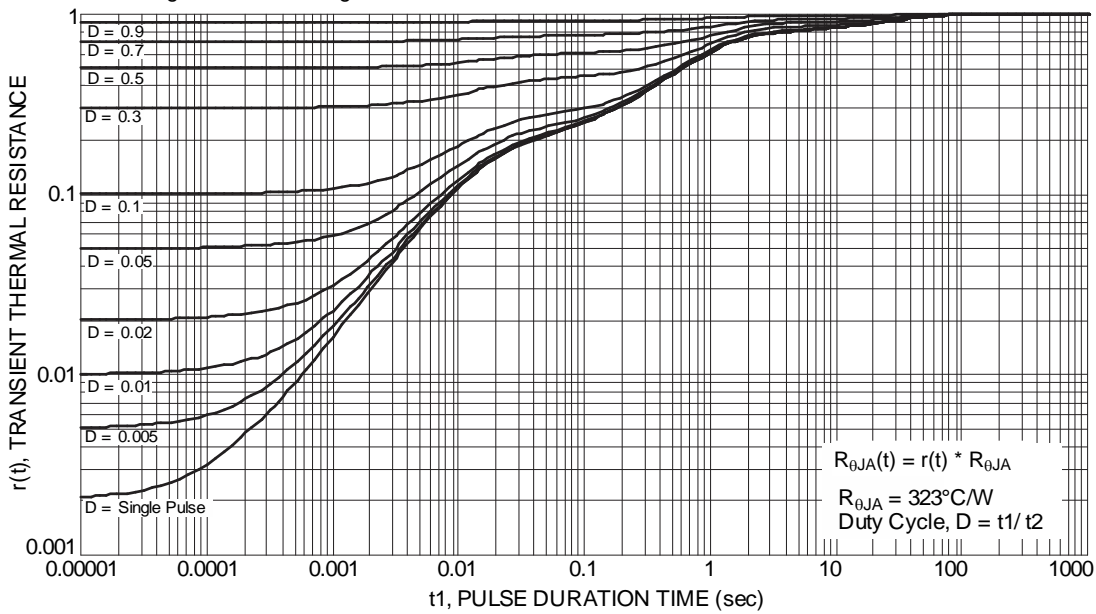
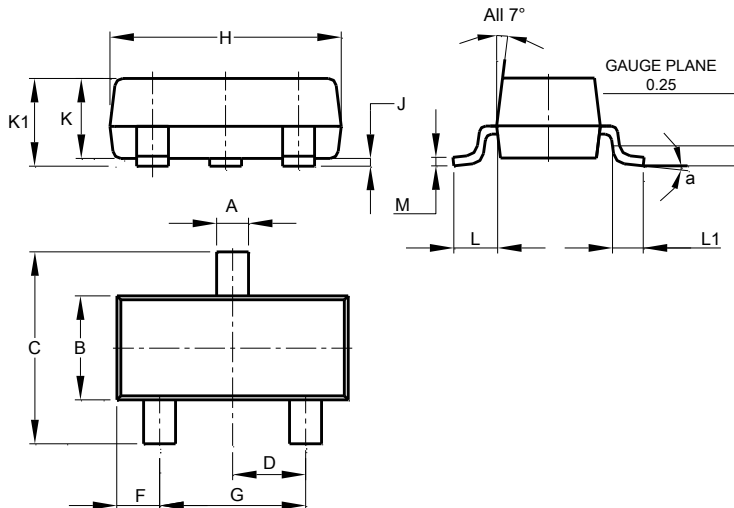


Figure 12 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23

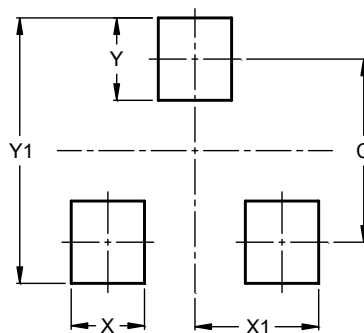


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9





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